Octal bus transceiver; 3-state

Rev. 1 — 21 March 2013

Product data sheet

1. General description

The 74AHC245-Q100; 74AHCT245-Q100 is a high-speed Si-gate CMOS device.

The 74AHC245-Q100; 74AHCT245-Q100 is an octal transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions.

The 74AHC245-Q100; 74AHCT245-Q100 features an output enable input (\overline{OE}), for easy cascading, and a send and receive direction control input (DIR).

 $\overline{\text{OE}}$ controls the outputs so that the buses are effectively isolated.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
- Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - For 74AHC245-Q100: CMOS level
 - For 74AHCT245-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

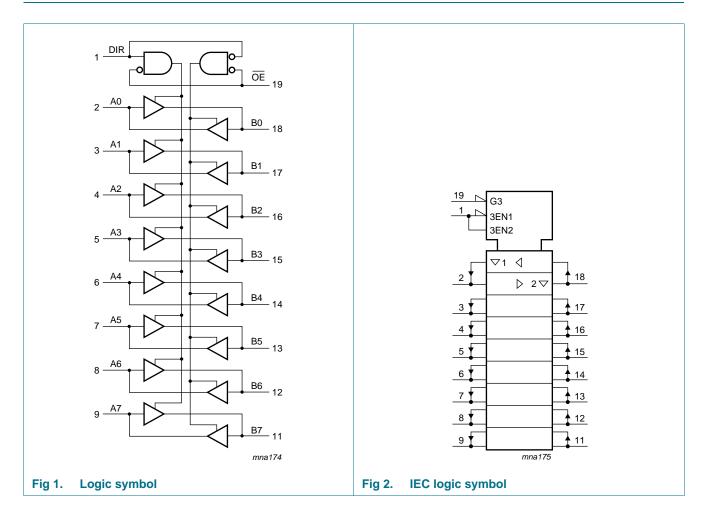


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3. Ordering information

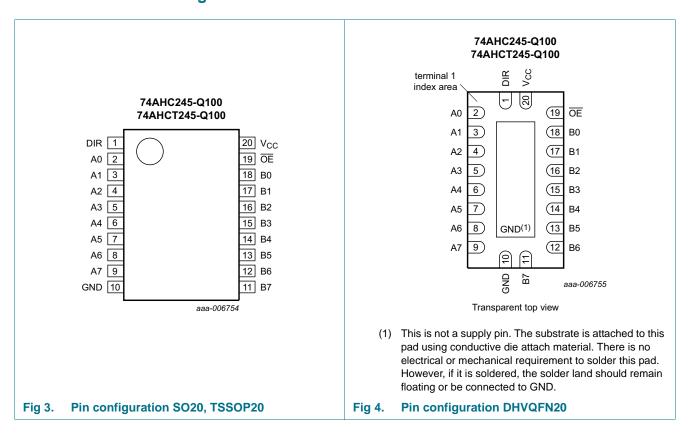
| Table 1.Ordering inType number | Package | | | | |
|--------------------------------|-------------------|----------|--|----------|--|
| | Temperature range | Name | Description | Version | |
| 74AHC245D-Q100 | –40 °C to +125 °C | SO20 | plastic small outline package; 20 leads; | SOT163-1 | |
| 74AHCT245D-Q100 | | | body width 7.5 mm | | |
| 74AHC245PW-Q100 | –40 °C to +125 °C | TSSOP20 | plastic thin shrink small outline package; 20 | SOT360-1 | |
| 74AHCT245PW-Q100 | | | leads; body width 4.4 mm | | |
| 74AHC245BQ-Q100 | –40 °C to +125 °C | DHVQFN20 | plastic dual in-line compatible thermal | SOT764-1 | |
| 74AHCT245BQ-Q100 | | | enhanced very thin quad flat package; no leads; 20 terminals; body $2.5 \times 4.5 \times 0.85$ mm | | |

4. Functional diagram



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5. Pinning information



5.2 Pin description

| Table 2.Pin description | | |
|--------------------------------|--------------------------------|----------------------------------|
| Symbol | Pin | Description |
| DIR | 1 | direction control input |
| A0, A1, A2, A3, A4, A5, A6, A7 | 2, 3, 4, 5, 6, 7, 8, 9 | data input/output |
| GND | 10 | ground (0 V) |
| B7, B6, B5, B4, B3, B2, B1, B0 | 11, 12, 13, 14, 15, 16, 17, 18 | data input/output |
| OE | 19 | output enable input (active LOW) |
| V _{CC} | 20 | supply voltage |

5.1 Pinning

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6. Functional description

| Table 3. | Function table ^[1] | | | | | | |
|----------|-------------------------------|--------------|--------------|--|--|--|--|
| Control | | Input/output | Input/output | | | | |
| OE | DIR | An | Bn | | | | |
| L | L | A = B | inputs | | | | |
| L | Н | inputs | B = A | | | | |
| Н | Х | Z | Z | | | | |

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | Min | Мах | Unit |
|------------------|-------------------------|--|----------------|------|------|
| V _{CC} | supply voltage | | -0.5 | +7.0 | V |
| VI | input voltage | | -0.5 | +7.0 | V |
| I _{IK} | input clamping current | V _I < -0.5 V | <u>[1]</u> –20 | - | mA |
| I _{OK} | output clamping current | $V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V | <u>[1]</u> –20 | +20 | mA |
| Ι _Ο | output current | $V_{\rm O}$ = –0.5 V to (V_{\rm CC} + 0.5 V) | -25 | +25 | mA |
| I _{CC} | supply current | | - | +75 | mA |
| I _{GND} | ground current | | -75 | - | mA |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| P _{tot} | total power dissipation | $T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$ | [2] _ | 500 | mW |

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO20 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K. For TSSOP20 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K. For DHVQFN20 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

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8. Recommended operating conditions

| Table 5. | Operating conditions | | | | | |
|-----------------------|-------------------------------------|-----------------------------------|-----|-----|-----------------|------|
| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
| 74AHC2 | 45-Q100 | | | | | |
| V _{CC} | supply voltage | | 2.0 | 5.0 | 5.5 | V |
| VI | input voltage | | 0 | - | 5.5 | V |
| Vo | output voltage | | 0 | - | V _{CC} | V |
| T _{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| $\Delta t / \Delta V$ | input transition rise and fall rate | V_{CC} = 3.0 V to 3.6 V | - | - | 100 | ns/V |
| | | V_{CC} = 4.5 V to 5.5 V | - | - | 20 | ns/V |
| 74AHCT | 245-Q100 | | | | | |
| V _{CC} | supply voltage | | 4.5 | 5.0 | 5.5 | V |
| VI | input voltage | | 0 | - | 5.5 | V |
| Vo | output voltage | | 0 | - | V _{CC} | V |
| T _{amb} | ambient temperature | | -40 | +25 | +125 | °C |
| $\Delta t / \Delta V$ | input transition rise and fall rate | $V_{CC} = 4.5 \text{ V}$ to 5.5 V | - | - | 20 | ns/V |

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | | 25 °C | | -40 °C 1 | to +85 °C | –40 °C t | o +125 °C | Unit |
|-----------------|-------------------------|--|------|-------|------|----------|-----------|----------|-----------|------|
| | | | Min | Тур | Max | Min | Max | Min | Max | |
| 74AHC2 | 45-Q100 | | | | | | | | | |
| VIH | HIGH-level | V _{CC} = 2.0 V | 1.5 | - | - | 1.5 | - | 1.5 | - | V |
| | input voltage | V _{CC} = 3.0 V | 2.1 | - | - | 2.1 | - | 2.1 | - | V |
| | | V _{CC} = 5.5 V | 3.85 | - | - | 3.85 | - | 3.85 | - | V |
| V _{IL} | LOW-level | V _{CC} = 2.0 V | - | - | 0.5 | - | 0.5 | - | 0.5 | V |
| | input voltage | V _{CC} = 3.0 V | - | - | 0.9 | - | 0.9 | - | 0.9 | V |
| | V _{CC} = 5.5 V | - | - | 1.65 | - | 1.65 | - | 1.65 | V | |
| 011 | HIGH-level | $V_{I} = V_{IH} \text{ or } V_{IL}$ | | | | | | | | |
| | output voltage | I_{O} = –50 $\mu\text{A};V_{CC}$ = 2.0 V | 1.9 | 2.0 | - | 1.9 | - | 1.9 | - | V |
| | | I_{O} = –50 $\mu\text{A};V_{CC}$ = 3.0 V | 2.9 | 3.0 | - | 2.9 | - | 2.9 | - | V |
| | | I_{O} = –50 $\mu\text{A};V_{CC}$ = 4.5 V | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V |
| | | $I_0 = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$ | 2.58 | - | - | 2.48 | - | 2.40 | - | V |
| | | $I_0 = -8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | 3.94 | - | - | 3.80 | - | 3.70 | - | V |
| V _{OL} | LOW-level | $V_{I} = V_{IH} \text{ or } V_{IL}$ | | | | | | | | |
| | output voltage | $I_0 = 50 \ \mu A; \ V_{CC} = 2.0 \ V$ | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | $I_0 = 50 \ \mu A; \ V_{CC} = 3.0 \ V$ | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | $I_0 = 50 \ \mu A; \ V_{CC} = 4.5 \ V$ | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I_{O} = 4.0 mA; V_{CC} = 3.0 V | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| | | $I_{O} = 8.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$ | - | - | 0.36 | - | 0.44 | - | 0.55 | V |

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Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

| Symbol | Parameter | Conditions | | 25 °C | | _40 °C ∙ | to +85 °C | –40 °C t | o +125 °C | Un |
|------------------|-----------------------------|---|------|-------|-------|----------|-----------|----------|-----------|----|
| | | | Min | Тур | Max | Min | Max | Min | Max | |
| l _l | input leakage current | V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V | - | - | 0.1 | - | 1.0 | - | 2.0 | μA |
| l _{oz} | OFF-state output current | | - | - | ±0.25 | - | ±2.5 | - | ±10.0 | μA |
| lcc | supply current | $\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$ | - | - | 4.0 | - | 40 | - | 80 | μA |
| Cı | input capacitance | $V_{I} = V_{CC} \text{ or } GND$ | - | 3 | 10 | - | 10 | - | 10 | pF |
| Co | output capacitance | | - | 4 | - | - | - | - | - | рF |
| 74AHCT | 245-Q100 | | | | | | | | | |
| V _{IH} | HIGH-level input voltage | V_{CC} = 4.5 V to 5.5 V | 2.0 | - | - | 2.0 | - | 2.0 | - | V |
| V _{IL} | LOW-level input voltage | V_{CC} = 4.5 V to 5.5 V | - | - | 0.8 | - | 0.8 | - | 0.8 | V |
| V _{он} | HIGH-level | V_{I} = V_{IH} or $V_{\text{IL}};$ V_{CC} = 4.5 V | | | | | | | | |
| output voltage | I _O = -50 μA | 4.4 | 4.5 | - | 4.4 | - | 4.4 | - | V | |
| | | I _O = -8.0 mA | 3.94 | - | - | 3.80 | - | 3.70 | - | V |
| V _{OL} | LOW-level | $V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$ | | | | | | | | |
| | output voltage | I _O = 50 μA | - | 0 | 0.1 | - | 0.1 | - | 0.1 | V |
| | | I _O = 8.0 mA | - | - | 0.36 | - | 0.44 | - | 0.55 | V |
| lı | input leakage current | $V_I = 5.5 V \text{ or GND};$ $V_{CC} = 0 V \text{ to } 5.5 V$ | - | - | 0.1 | - | 1.0 | - | 2.0 | μA |
| I _{OZ} | OFF-state output current | | - | - | ±0.25 | - | ±2.5 | - | ±10.0 | μA |
| I _{CC} | supply current | | - | - | 4.0 | - | 40 | - | 80 | μA |
| ∆l _{CC} | additional supply current | per input pin; $V_I = V_{CC} - 2.1 \text{ V};$ other pins at V_{CC} or GND; $I_O = 0 \text{ A}; V_{CC} = 4.5 \text{ V}$ to 5.5 V | - | - | 1.35 | - | 1.5 | - | 1.5 | m/ |
| CI | input capacitance | $V_I = V_{CC}$ or GND | - | 3 | 10 | - | 10 | - | 10 | рF |
| Co | output capacitance | | - | 4 | - | - | - | - | - | pF |

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10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

| Symbol | Parameter | Conditions | | | 25 °C | | _40 °C | to +85 °C | –40 °C 1 | o +125 °C | Uni |
|-----------------------------|--|---|------------|-----|-----------------|---------------|---------|-----------|----------|------------------------|---------|
| | | | | Min | Typ[1] | Max | Min | Max | Min | Max | |
| 74AHC2 | 45-Q100 | | | | | | | | | | |
| pd | propagation delay | An to Bn; Bn to An; see <u>Figure 5</u> | [2] | | | | | | | | |
| | | V_{CC} = 3.0 V to 3.6 V | | | | | | | | | |
| | | C _L = 15 pF | | - | 5.0 | 8.4 | 1.0 | 10.0 | 1.0 | 10.5 | ns |
| | | C _L = 50 pF | | - | 6.5 | 11.9 | 1.0 | 13.5 | 1.0 | 15.0 | ns |
| | | V_{CC} = 4.5 V to 5.5 V | | | | | | | | | |
| | | C _L = 15 pF | | - | 3.5 | 5.5 | 1.0 | 6.5 | 1.0 | 7.0 | ns |
| | | C _L = 50 pF | | | 5.0 | 7.5 | 1.0 | 8.5 | 1.0 | 9.5 | ns |
| t _{en} enable time | OE to An; OE to Bn; signal name DIR; see <u>Figure 6</u> | [3] | | | | | | | | | |
| | | V_{CC} = 3.0 V to 3.6 V | | | | | | | | | |
| | | C _L = 15 pF | | - | 6.5 | 13.2 | 1.0 | 15.5 | 1.0 | 16.5 | ns |
| | | C _L = 50 pF | | - | 9.0 | 16.7 | 1.0 | 19.0 | 1.0 | 21.0 | ns |
| | | V_{CC} = 4.5 V to 5.5 V | | | | | | | | | |
| | | C _L = 15 pF | | - | 4.0 | 8.5 | 1.0 | 10.0 | 1.0 | 11.0 | ns |
| | | C _L = 50 pF | | - | 5.0 | 10.6 | 1.0 | 12.0 | 1.0 | 13.5 | ns |
| disable time | disable time | OE to An; OE to Bn; signal name DIR; see <u>Figure 6</u> | <u>[4]</u> | | | | | | | | |
| | | V_{CC} = 3.0 V to 3.6 V | | | | | | | | | |
| | | C _L = 15 pF | | - | 7.5 | 12.5 | 1.0 | 15.5 | 1.0 | 16.0 | ns |
| | | $C_L = 50 \text{ pF}$ | | - | 10.0 | 15.8 | 1.0 | 18.0 | 1.0 | 20.0 | ns |
| | | V_{CC} = 4.5 V to 5.5 V | | | | | | | | | |
| | | C _L = 15 pF | | - | 4.5 | 7.8 | 1.0 | 9.2 | 1.0 | 10.0 | ns |
| | | C _L = 50 pF | | - | 6.0 | 9.7 | 1.0 | 11.0 | 1.0 | 12.5 | ns |
| C _{PD} | power dissipation capacitance | $f_i = 1 \text{ MHz};$ V _I = GND to V _{CC} | [5] | - | 12 | - | - | - | - | - | pF |
| 74AHCT | 245-Q100; V _C | _C = 4.5 V to 5.5 V | | | | | | | | | |
| t _{pd} | propagation delay | An to Bn; Bn to An; see <u>Figure 5</u> | [2] | | | | | | | | |
| | | C _L = 15 pF | | - | 3.5 | 7.7 | 1.0 | 8.5 | 1.0 | 10.0 | ns |
| | | C _L = 50 pF | | - | 4.5 | 8.7 | 1.0 | 9.5 | 1.0 | 11.0 | ns |
| en | enable time | OE to An; OE to Bn; signal name DIR; see <u>Figure 6</u> | <u>[3]</u> | | | | | | | | |
| | | C _L = 15 pF | | - | 5.0 | 13.8 | 1.0 | 15.0 | 1.0 | 17.5 | ns |
| | | C _L = 50 pF | | - | 6.0 | 14.8 | 1.0 | 16.0 | 1.0 | 18.5 | ns |
| | 45_Q100 | All 1. C | | | nent is subject | to logal disc | laimara | | © N | XP B.V. 2013. All righ | to rook |

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| Symbol | Parameter | Conditions | | 25 °C | | –40 °C to +85 °C | | –40 °C to +125 °C | | Unit |
|-------------------------------|-------------------------------------|---|-----|--------|------|------------------|------|-------------------|------|------|
| | | | Min | Typ[1] | Max | Min | Max | Min | Max | |
| t _{dis} disable time | | OE to An; OE to Bn; [4] signal name DIR; see Figure 6 | | | | | | | | |
| | | C _L = 15 pF | - | 5.0 | 14.4 | 1.0 | 15.5 | 1.0 | 18.0 | ns |
| | | C _L = 50 pF | - | 6.0 | 15.4 | 1.0 | 16.5 | 1.0 | 19.5 | ns |
| C _{PD} | power dissipation capacitance | $f_i = 1 \text{ MHz};$ [5] V _I = GND to V _{CC} | - | 15 | - | - | - | - | - | pF |

Table 7. Dynamic characteristics ... continued

[1] Typical values are measured at nominal supply voltage ($V_{CC} = 3.3$ V and $V_{CC} = 5.0$ V).

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

- [3] t_{en} is the same as t_{PZL} and t_{PZH} .
- [4] t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma (C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

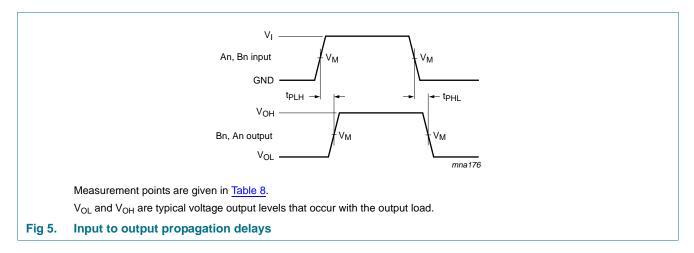
 C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

10.1 Waveforms



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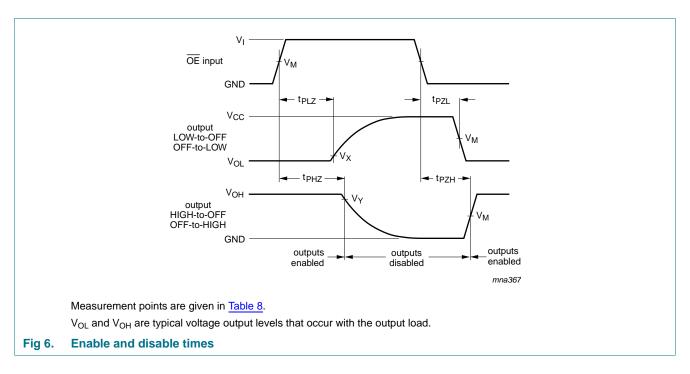


Table 8.Measurement points

| Туре | Input | Output | Output | | | | | |
|----------------|--------------------|----------------------------|-------------------------|-------------------------|--|--|--|--|
| | V _M | V _M | V _X | V _Y | | | | |
| 74AHC245-Q100 | $0.5\times V_{CC}$ | $0.5 \times V_{\text{CC}}$ | V _{OL} + 0.3 V | $V_{OH} - 0.3 \ V$ | | | | |
| 74AHCT245-Q100 | 1.5 V | $0.5\times V_{CC}$ | V _{OL} + 0.3 V | V _{OH} – 0.3 V | | | | |

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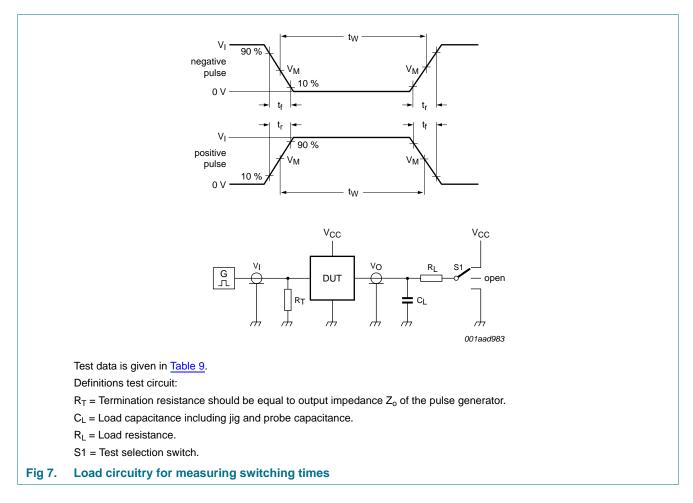


Table 9. Test data

| Туре | Input | | Load | Load | | S1 position | | |
|----------------|-----------------|---------------------------------|--------------|------|-------------------------------------|-------------------------------------|-------------------------------------|--|
| | VI | t _r , t _f | CL | RL | t _{PHL} , t _{PLH} | t _{PZH} , t _{PHZ} | t _{PZL} , t _{PLZ} | |
| 74AHC245-Q100 | V _{CC} | \leq 3.0 ns | 15 pF, 50 pF | 1 kΩ | open | GND | V _{CC} | |
| 74AHCT245-Q100 | 3.0 V | \leq 3.0 ns | 15 pF, 50 pF | 1 kΩ | open | GND | V _{CC} | |

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11. Package outline

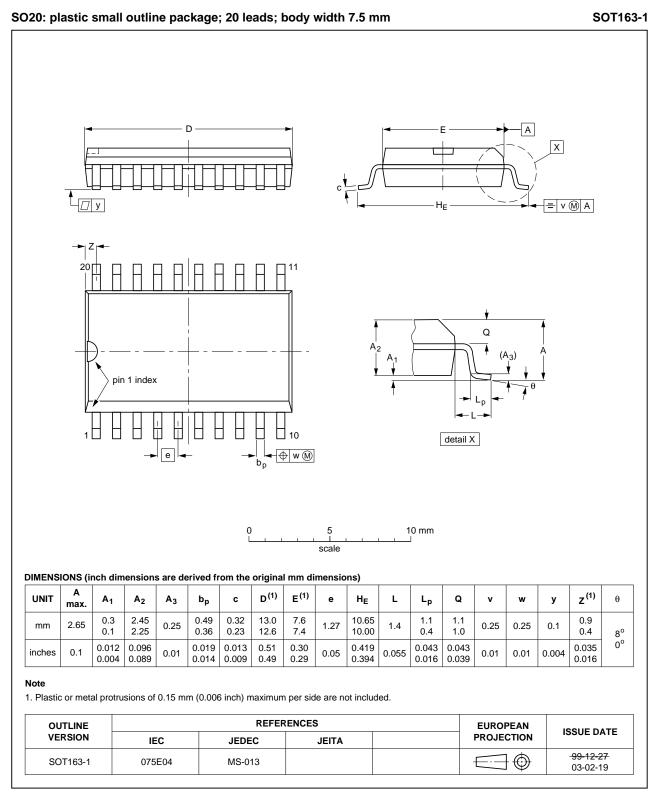


Fig 8. Package outline SOT163-1 (SO20)

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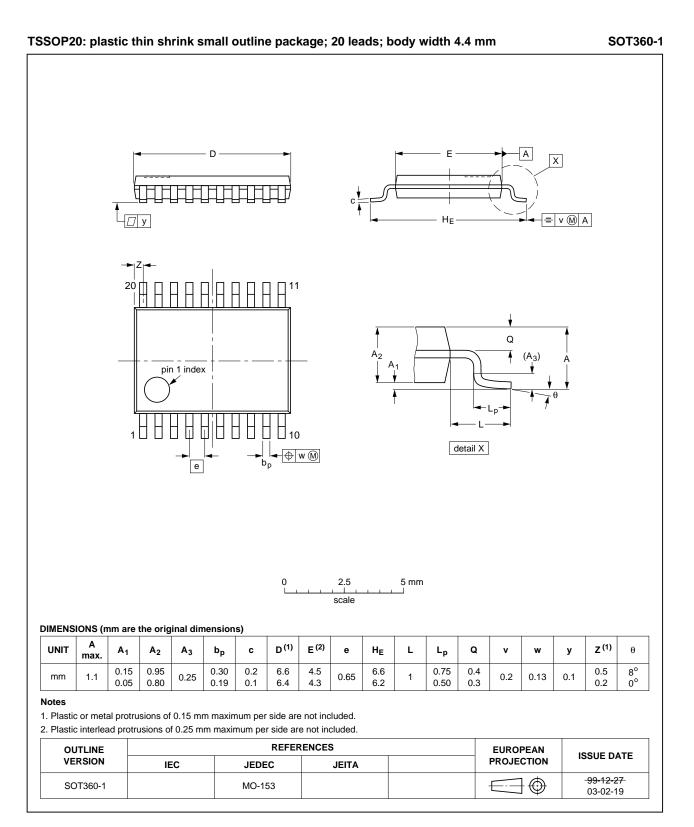
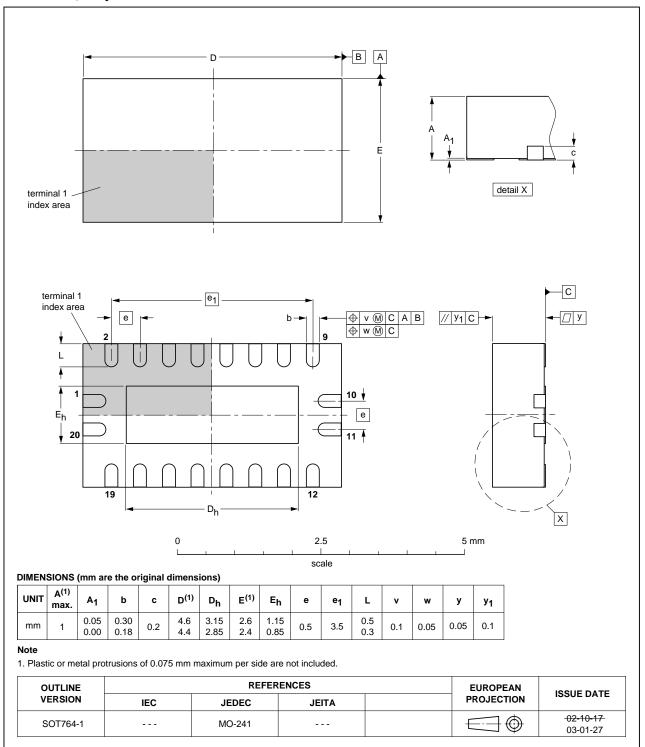


Fig 9. Package outline SOT360-1 (TSSOP20)

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DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 x 4.5 x 0.85 mm SOT764-1

Fig 10. Package outline SOT764-1 (DHVQFN20)

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12. Abbreviations

| AcronymDescriptionCDMCharged Device ModelCMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelMILMilitaryTTLTransistor-Transistor Logic | Table 10. | Abbreviations |
|---|-----------|---|
| CMOSComplementary Metal-Oxide SemiconductorDUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelMILMilitary | Acronym | Description |
| DUTDevice Under TestESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelMILMilitary | CDM | Charged Device Model |
| ESDElectroStatic DischargeHBMHuman Body ModelMMMachine ModelMILMilitary | CMOS | Complementary Metal-Oxide Semiconductor |
| HBM Human Body Model MM Machine Model MIL Military | DUT | Device Under Test |
| MM Machine Model MIL Military | ESD | ElectroStatic Discharge |
| MIL Military | HBM | Human Body Model |
| | MM | Machine Model |
| TTI Transistor-Transistor Logic | MIL | Military |
| | TTL | Transistor-Transistor Logic |

13. Revision history

| Table 11. Revision history | | | | |
|----------------------------|--------------|--------------------|---------------|------------|
| Document ID | Release date | Data sheet status | Change notice | Supersedes |
| 74AHC_AHCT245_Q100 v.1 | 20130321 | Product data sheet | - | - |

14. Legal information

14.1 Data sheet status

| Document status[1][2] | Product status ^[3] | Definition |
|--------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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